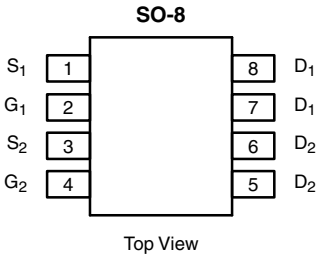
N- and P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
N-Channel	30	0.053 at V_{GS} = 10 V	4.9
		0.075 at V_{GS} = 4.5 V	4.1
P-Channel	- 30	0.080 at V_{GS} = - 10 V	- 3.9
		0.135 at V_{GS} = - 4.5 V	- 3.0

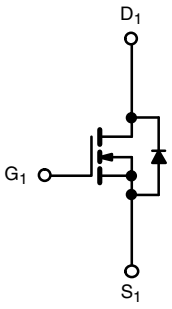
FEATURES

- **Halogen-free According to IEC 61249-2-21 Available**
- TrenchFET® Power MOSFETs
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

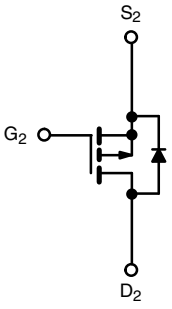
Pb-free
RoHS COMPLIANT
HALOGEN FREE Available



Ordering Information:
Si4532ADY-T1-E3 (Lead (Pb-free)
Si4532ADY-T1-GE3 (Lead (Pb-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter		Symbol	N-Channel		P-Channel		Unit
			10 s	Steady State	10 s	Steady State	
Drain-Source Voltage		V_{DS}	30		- 30		V
Gate-Source Voltage		V_{GS}	± 20		± 20		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	4.9	3.7	- 3.9	- 3.0	A
	T_A = 70 °C		3.9	2.9	- 3.1	- 2.4	
Pulsed Drain Current		I_{DM}	20				
Continuous Source Current (Diode Conduction)[a]		I_S	1.7	0.94	- 1.7	- 1.0	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2	1.13	2	1.2	W
	T_A = 70 °C		1.3	0.73	1.3	0.76	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	N-Channel		P-Channel		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	55	62.5	54	62.5	°C/W
	Steady State		90	110	87	105	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	40	50	34	45	

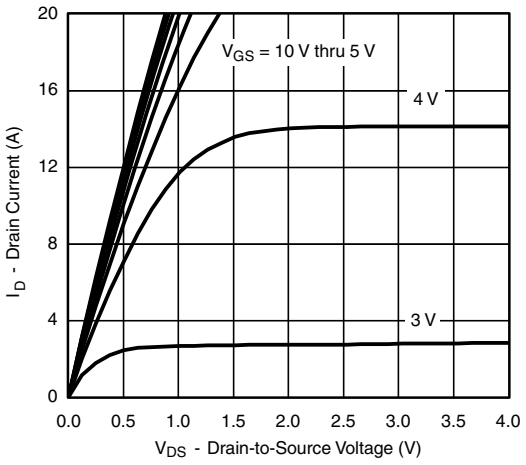
Note:
a. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.**	**Max.**	**Unit**
Static							
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	1			V
		V_{DS} = V_{GS}, I_D = - 250 µA	P-Ch	- 1			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	N-Ch			± 100	nA
		V_{DS} = 0 V, V_{GS} = ± 20 V	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	N-Ch			1	µA
		V_{DS} = - 30 V, V_{GS} = 0 V	P-Ch			- 1	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C	N-Ch			5	
		V_{DS} = - 30 V, V_{GS} = 0 V, T_J = 55 °C	P-Ch			- 5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	N-Ch	20			A
		V_{DS} ≤ - 5 V, V_{GS} = - 10 V	P-Ch	- 20			
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 4.9 A	N-Ch		0.044	0.053	Ω
		V_{GS} = - 10 V, I_D = - 3.9 A	P-Ch		0.062	0.080	
		V_{GS} = 4.5 V, I_D = 4.1 A	N-Ch		0.062	0.075	
		V_{GS} = - 4.5 V, I_D = - 3 A	P-Ch		0.105	0.135	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 4.9 A	N-Ch		11		S
		V_{DS} = - 15 V, I_D = - 2.5 A	P-Ch		5		
Diode Forward Voltage[a]	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V	N-Ch		0.80	1.2	V
		I_S = - 1.7 A, V_{GS} = 0 V	P-Ch		- 0.82	- 1.2	
Dynamic[b]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 10 V, V_{GS} = 10 V, I_D = 4.9 A P-Channel V_{DS} = - 4 V, V_{GS} = - 10 V, I_D = - 3.9 A	N-Ch		8	16	nC
			P-Ch		10	20	
Gate-Source Charge	Q_{gs}		N-Ch		1.4		
			P-Ch		2		
Gate-Drain Charge	Q_{gd}		N-Ch		1.2		
			P-Ch		1.9		
Gate Resistancee	R_g	f = 1 MHz	N-Ch	0.4	1.6	3.2	Ω
			P-Ch	1.5	6.2	12	
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 10 V, R_L = 10 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_g = 6 Ω P-Channel V_{DD} = - 10 V, R_L = 10 Ω I_D ≅ - 1 A, V_{GEN} = - 10 V, R_g = 6 Ω	N-Ch		12	20	ns
			P-Ch		8	15	
Rise Time	t_r		N-Ch		10	20	
			P-Ch		9	18	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		23	45	
			P-Ch		21	40	
Fall Time	t_f		N-Ch		8	15	
			P-Ch		10	20	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, dI/dt = 100 A/µs	N-Ch		25	40	
		I_F = - 1.7 A, dI/dt = 100 A/µs	P-Ch		27	40	

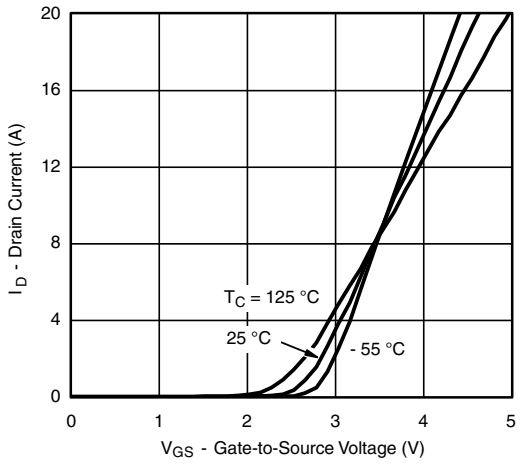
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

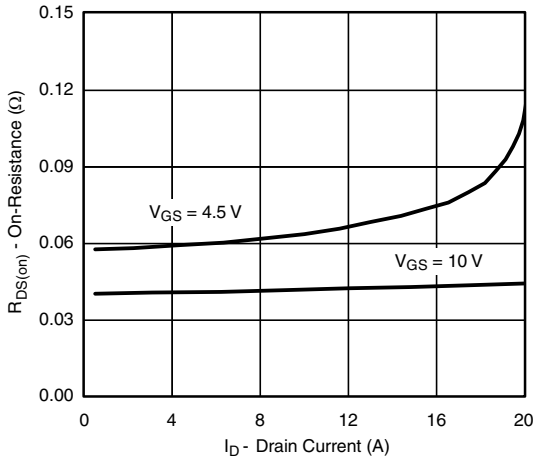
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



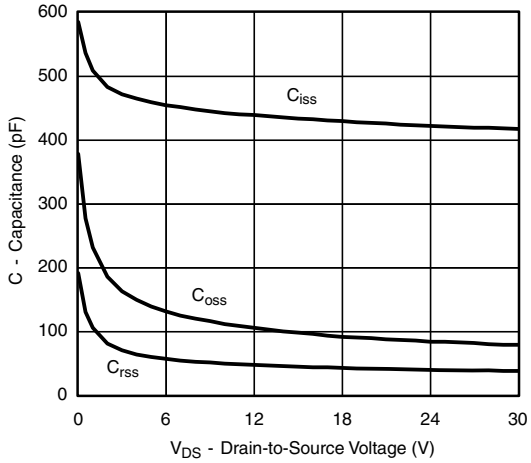
Output Characteristics



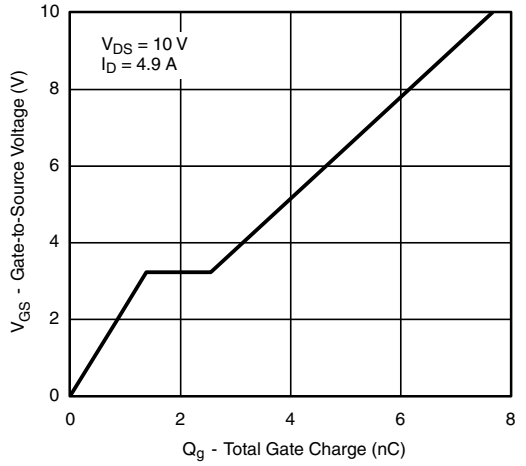
Transfer Characteristics



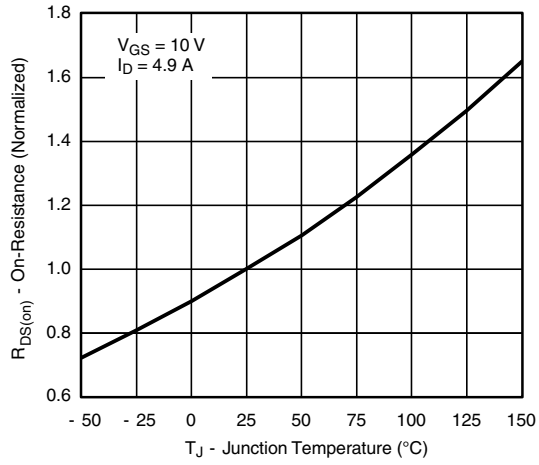
On-Resistance vs. Drain Current



Capacitance

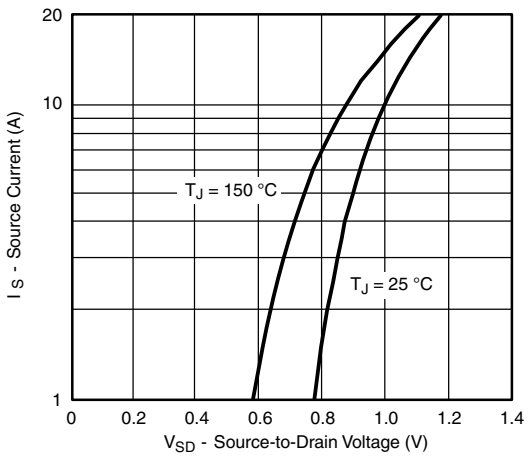


Gate Charge

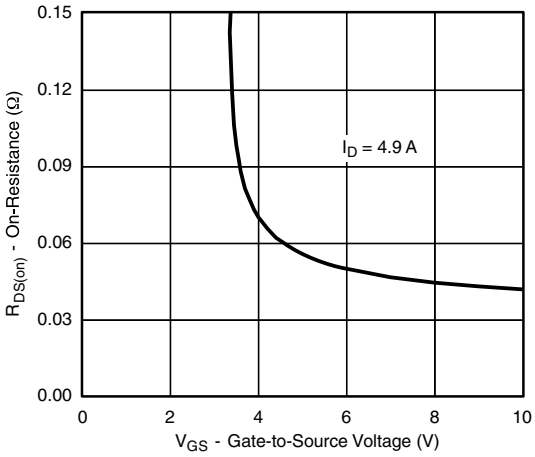


On-Resistance vs. Junction Temperature

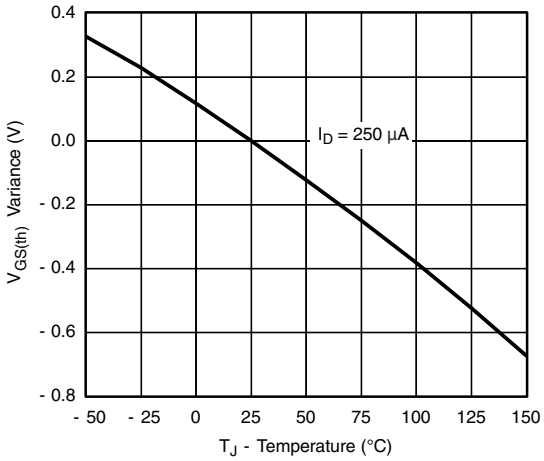
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



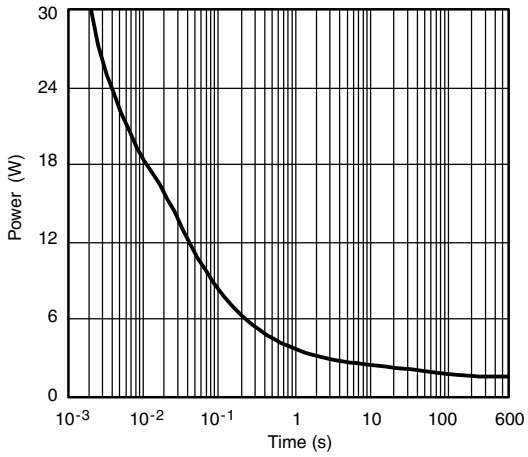
Source-Drain Diode Forward Voltage



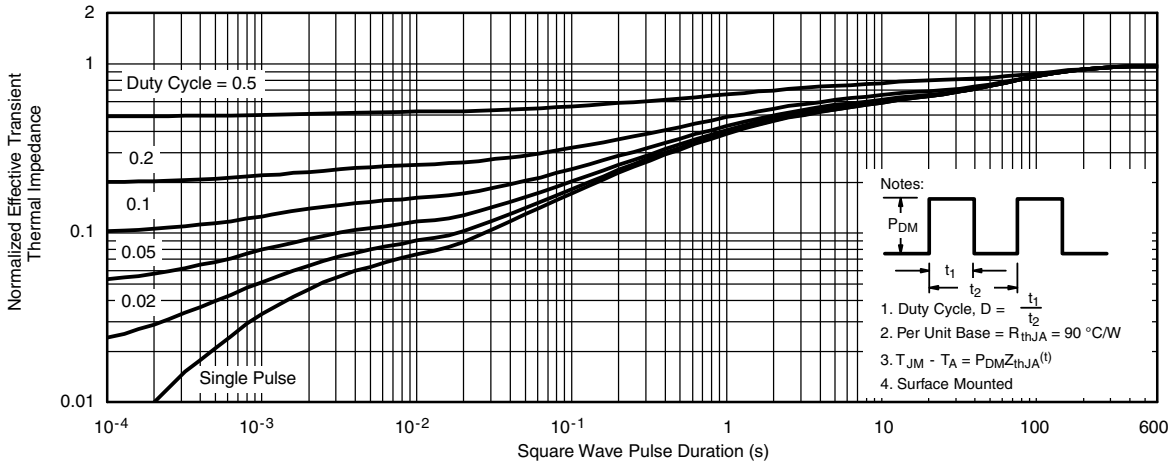
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



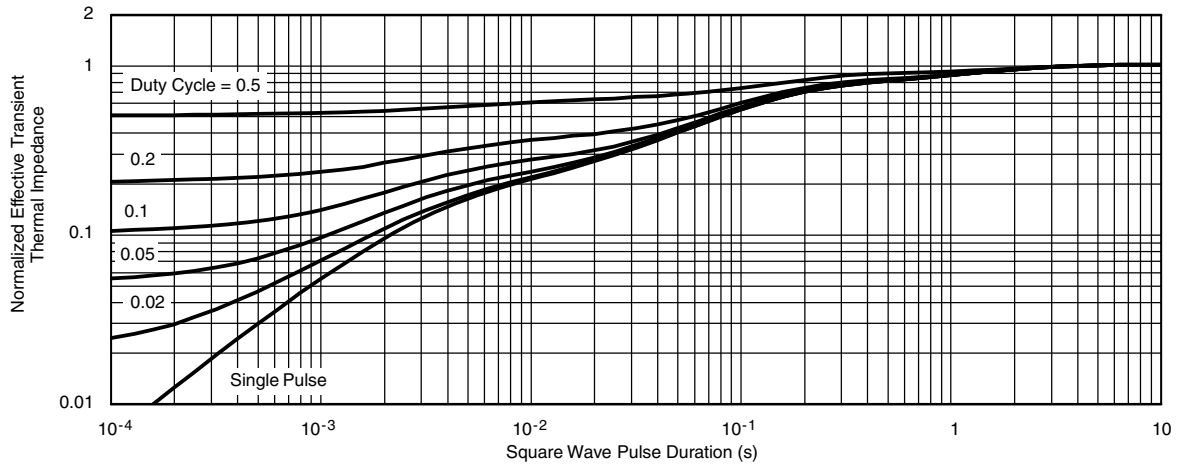
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

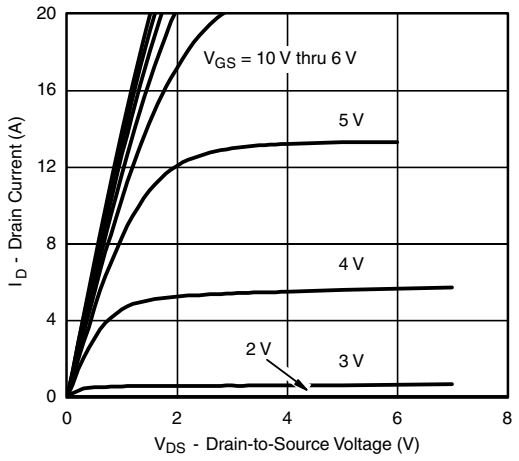
Document Number: 71133
S11-1908-Rev. D, 26-Sep-11

N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

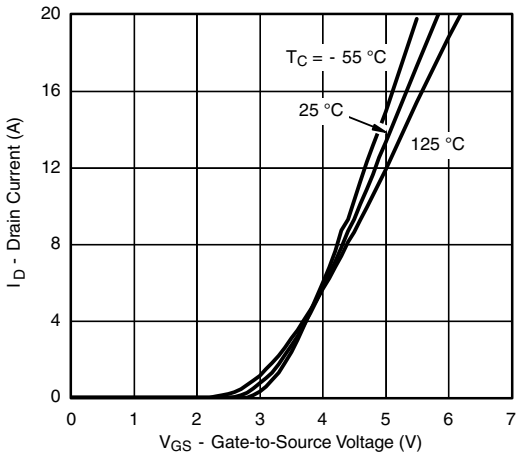


Normalized Thermal Transient Impedance, Junction-to-Foot

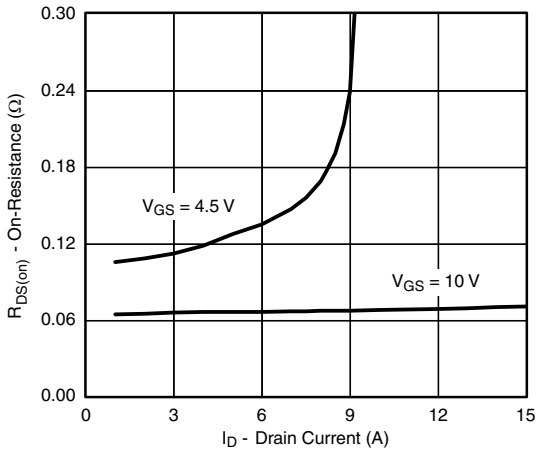
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



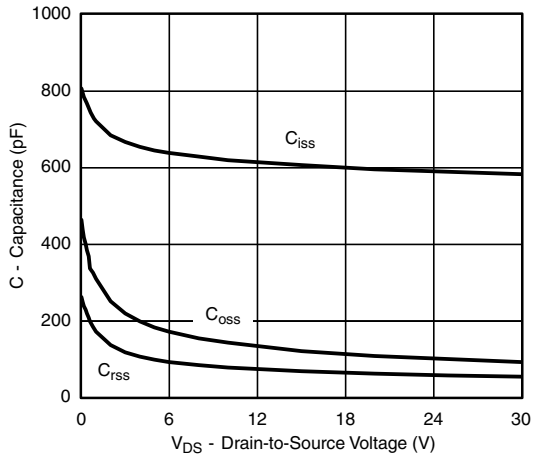
Output Characteristics



Transfer Characteristics

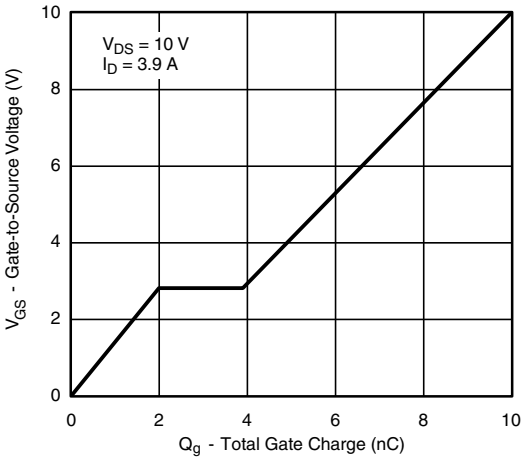


On-Resistance vs. Drain Current

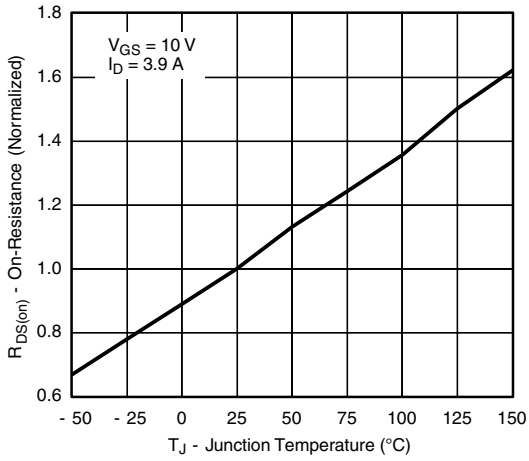


Capacitance

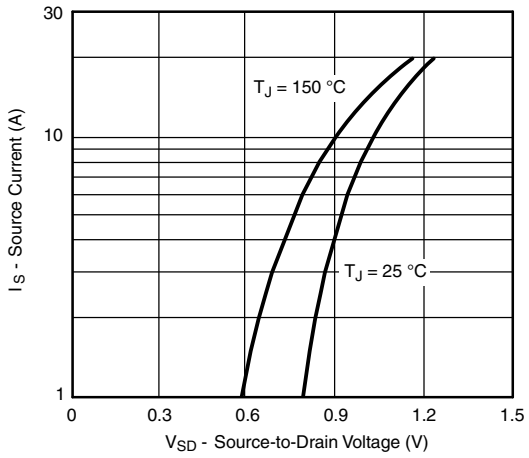
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



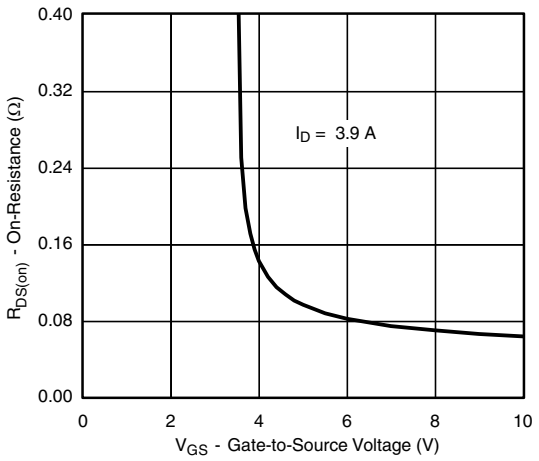
Gate Charge



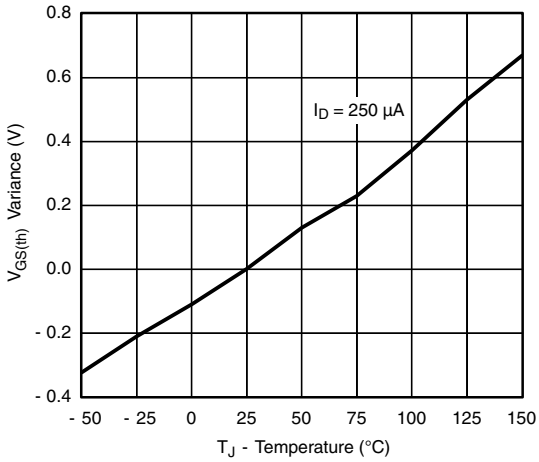
On-Resistance vs. Junction Temperature



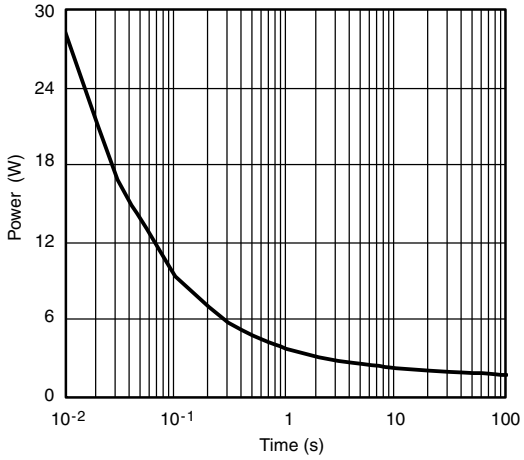
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

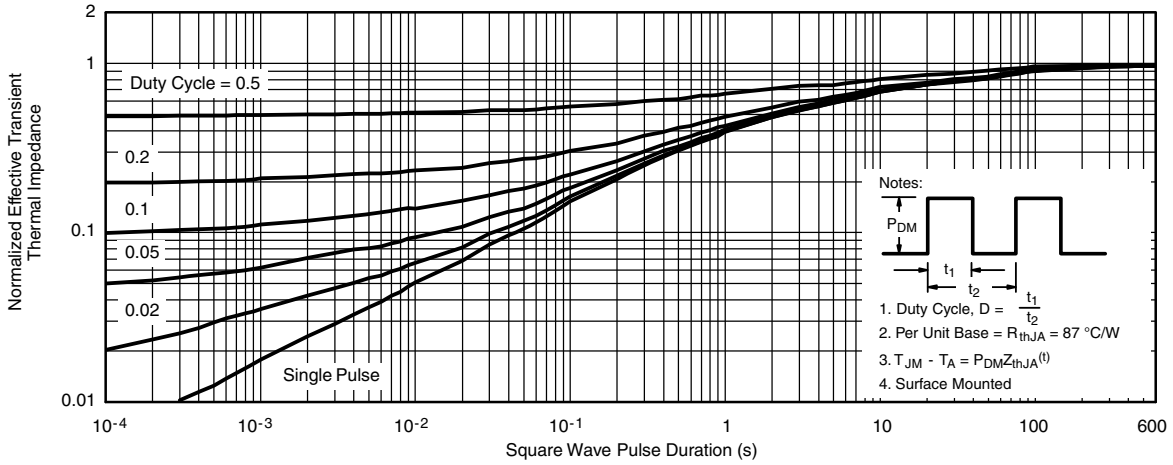


Threshold Voltage

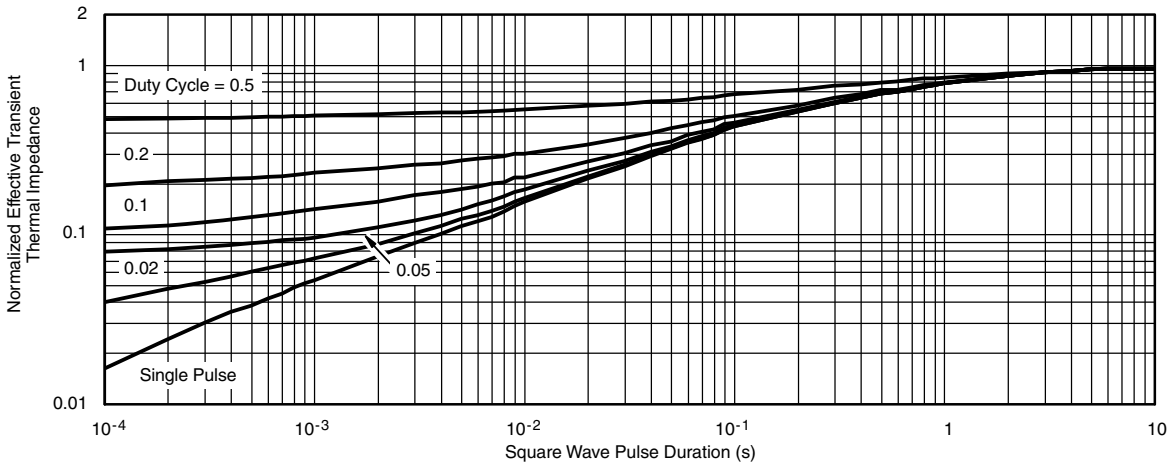


Single Pulse Power, Junction-to-Ambient

P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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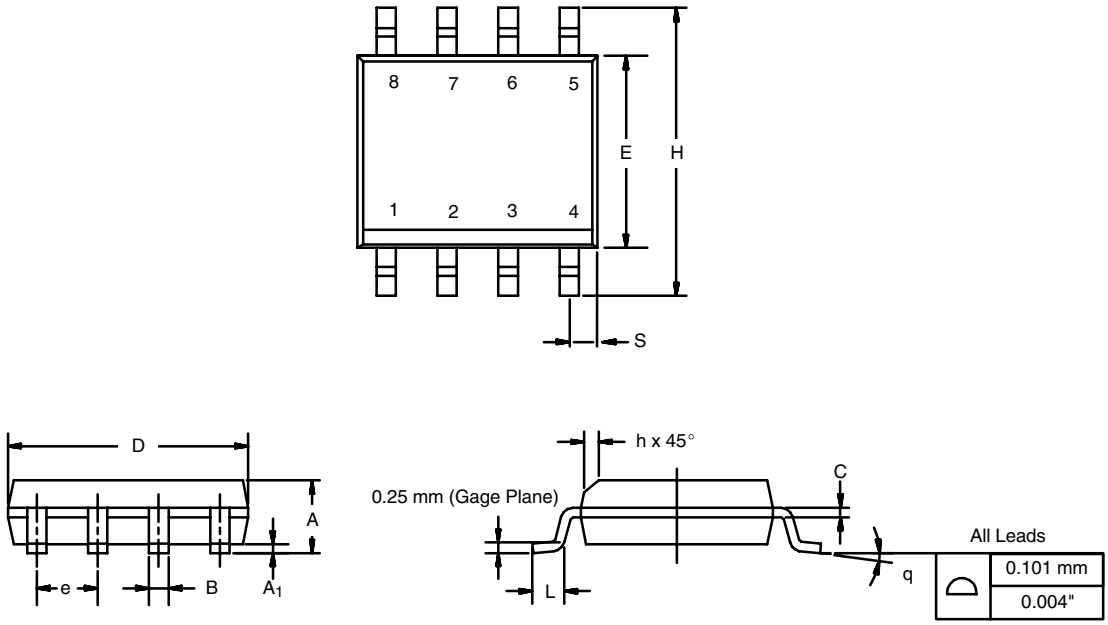
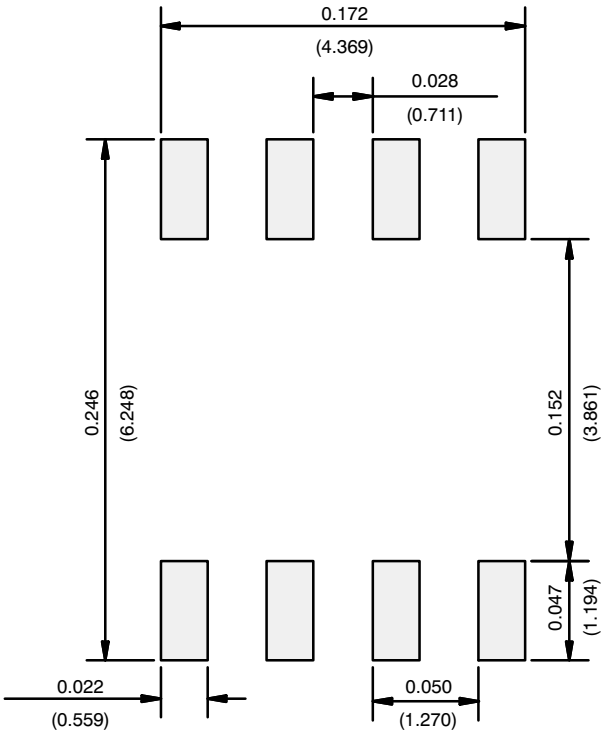
SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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